

AUDIO FREQUENCY GENERAL PURPOSE AMPLIFIER
NPN SILICON EPITAXIAL TRANSISTOR
MINI MOLD

FEATURES

- High DC Current Gain: $h_{FE} = 200$ TYP.
($V_{CE} = 6.0$ V, $I_C = 1.0$ mA)
- High Voltage: $V_{CEO} = 50$ V

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Current ($T_A = 25$ °C)

Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	100	mA

Maximum Power Dissipation

Total Power Dissipation			
at 25 °C Ambient Temperature	P_T	200	mW

Maximum Temperatures

Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C)

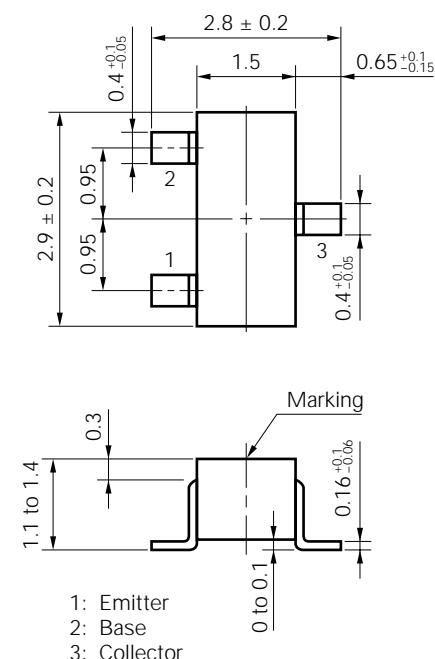
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I_{CBO}			0.1	μA	$V_{CB} = 60$ V, $I_E = 0$
Emitter Cutoff Current	I_{EBO}			0.1	μA	$V_{EB} = 5.0$ V, $I_C = 0$
DC Current Gain	h_{FE}	90	200	600		$V_{CE} = 6.0$ V, $I_C = 1.0$ mA*
Collector Saturation Voltage	$V_{CE(sat)}$		0.15	0.3	V	$I_C = 100$ mA, $I_B = 10$ mA*
Base to Saturation Voltage	$V_{BE(sat)}$		0.86	1.0	V	$I_C = 100$ mA, $I_B = 10$ mA*
Base Emitter Voltage	V_{BE}	0.55	0.62	0.65	V	$V_{CE} = 6.0$ V, $I_C = 1.0$ mA*
Gain Bandwidth Product	f_T		250		MHz	$V_{CE} = 6.0$ V, $I_E = -10$ mA
Output Capacitance	C_{ob}		3.0		pF	$V_{CB} = 6.0$ V, $I_E = 0$, $f = 1.0$ MHz

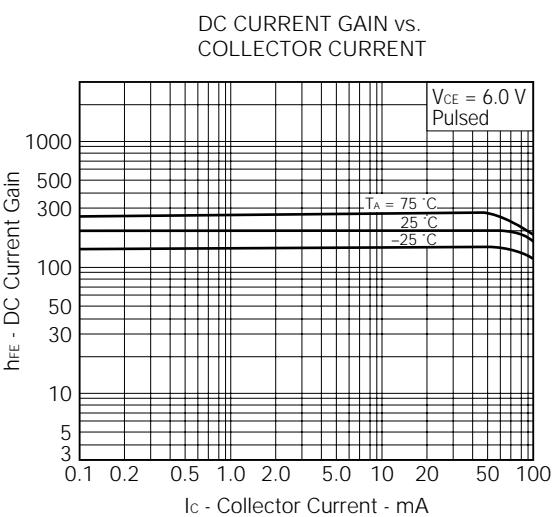
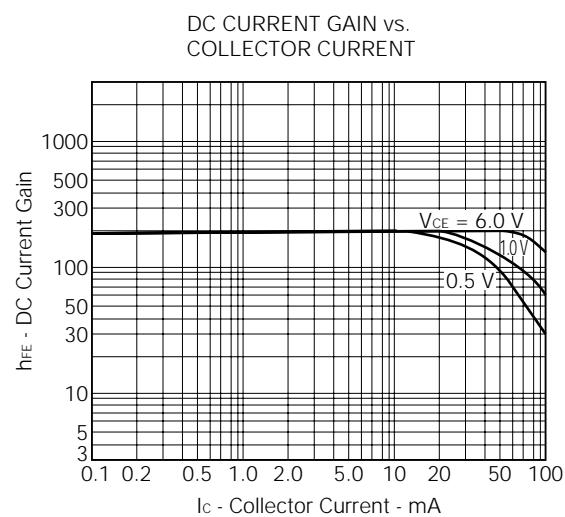
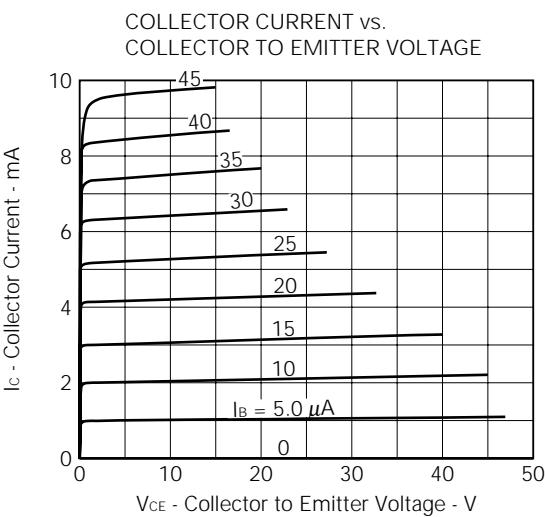
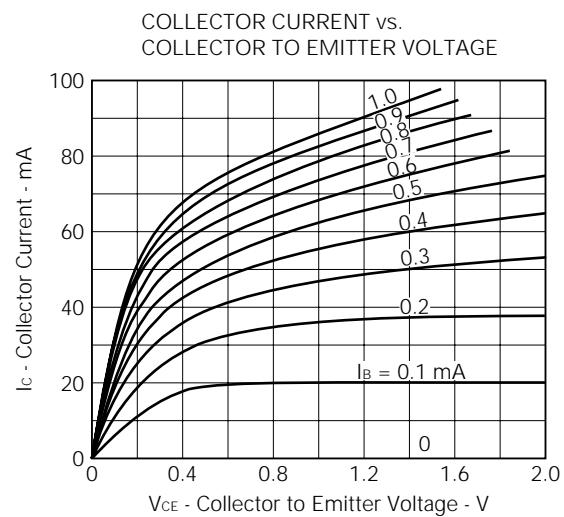
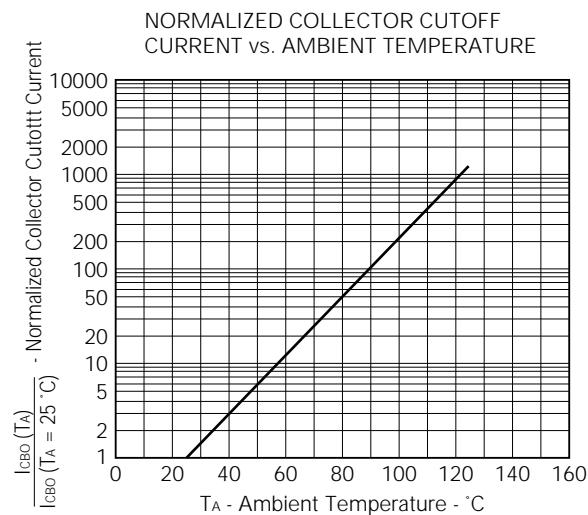
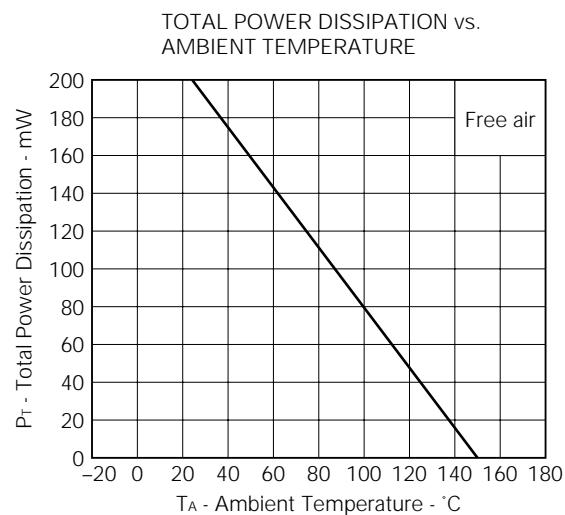
* Pulsed: $PW \leq 350$ μs , Duty Cycle ≤ 2 % h_{FE} Classification

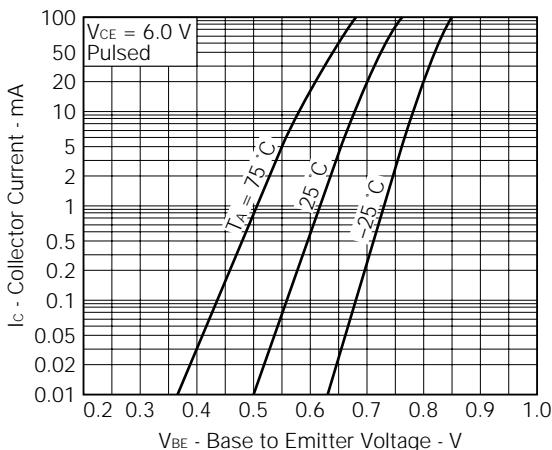
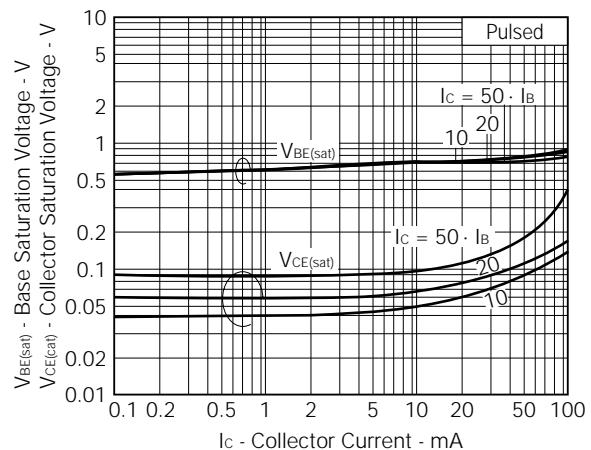
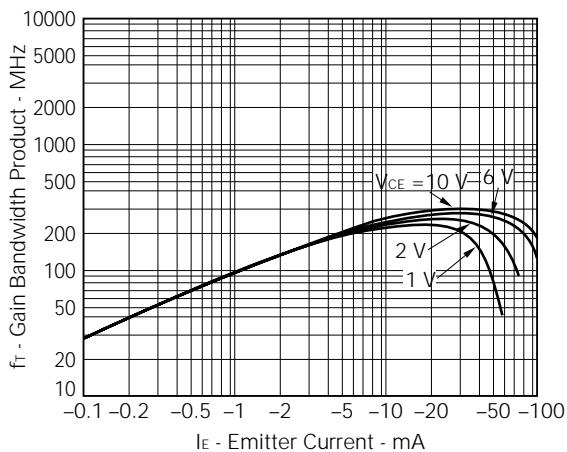
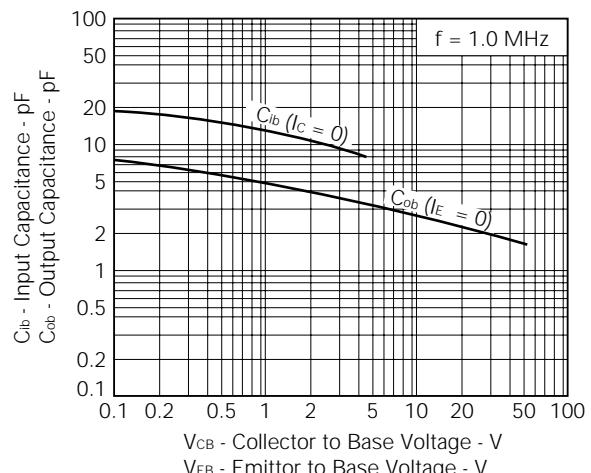
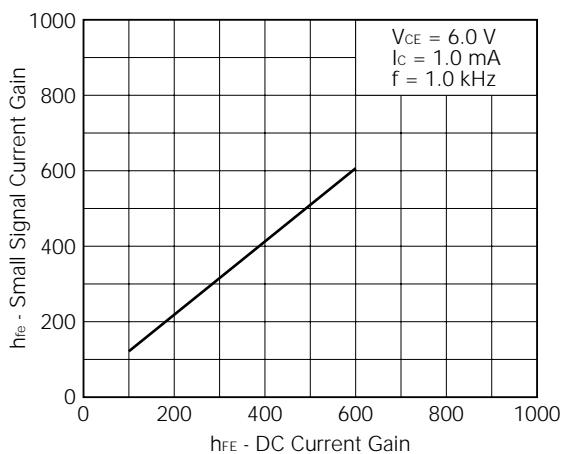
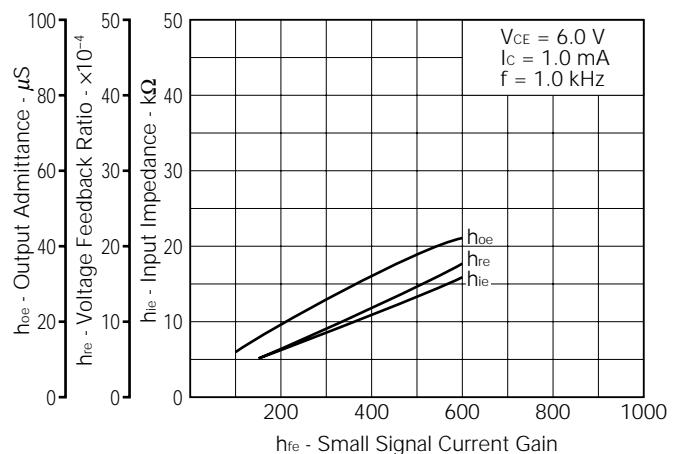
Marking	L4	L5	L6	L7
h_{FE}	90 to 180	135 to 270	200 to 400	300 to 600

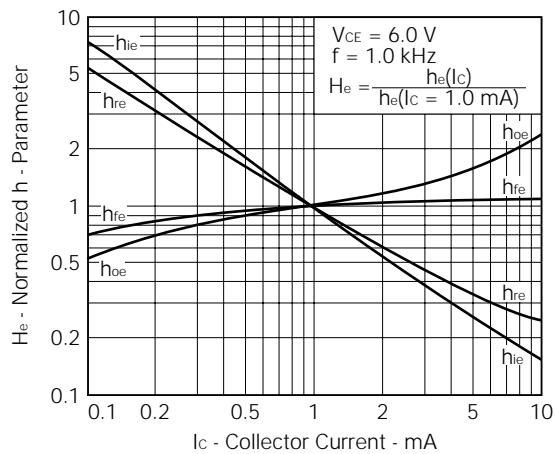
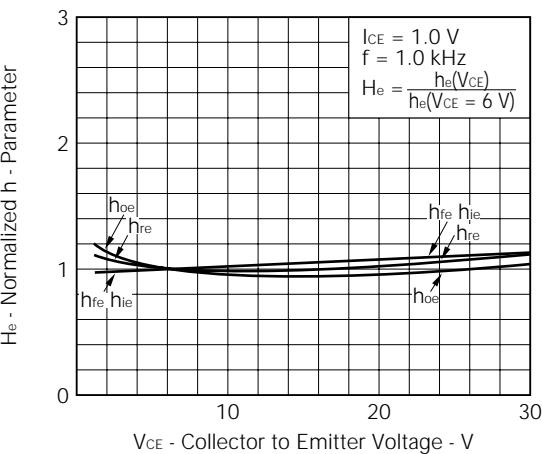
PACKAGE DIMENSIONS

in millimeters



TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

COLLECTOR CURRENT vs.
BASE TO Emitter VOLTAGECOLLECTOR AND BASE SATURATION
VOLTAGE vs. COLLECTOR CURRENTGAIN BANDWIDTH PRODUCT vs.
EMITTER CURRENTINPUT AND OUTPUT CAPACITANCE
vs. REVERSE VOLTAGESMALL SIGNAL CURRENT GAIN vs.
DC CURRENT GAININPUT IMPEDANCE VOLTAGE FEEDBACK
RATIO AND OUTPUT ADMITTANCE vs.
SMALL SIGNAL CURRENT GAIN

NORMALIZED h-PARAMETER vs.
COLLECTOR CURRENTNORMALIZED h-PARAMETER vs.
COLLECTOR TO Emitter VOLTAGE

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Anti-radioactive design is not implemented in this product.